

Title (en)
INTEGRATED READ-ONLY MEMORY, METHOD FOR OPERATING SAID READ-ONLY MEMORY AND CORRESPONDING PRODUCTION METHOD

Title (de)
INTEGRIERTER FESTWERTSPEICHER, VERFAHREN ZUM BETREIBEN EINES SOLCHEN FESTWERTSPEICHERS SOWIE HERSTELLUNGSVERFAHREN

Title (fr)
MEMOIRE ROM INTEGREE, PROCEDE POUR FAIRE FONCTIONNER UNE TELLE MEMOIRE ROM, ET PROCEDE DE PRODUCTION D'UNE TELLE MEMOIRE

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Application
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• EP 0301583 W 20030217

Abstract (en)
[origin: WO03075350A1] The invention relates an integrated read-only memory containing select transistors, each of which has a drain connection and an electrode for feeding a voltage or current. A layer is provided between the drain connections and the electrode, whose electric resistance can be changed under the effect of a configuration voltage or current. The layer is applied in a backend process.

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IPC 8 full level
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